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RJK0358DPA Silicon N Channel Power MOS FET Power Switching

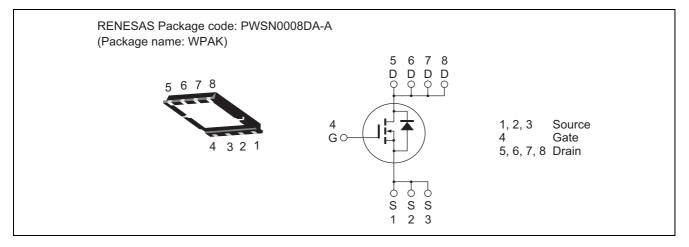
> REJ03G1651-0400 Rev.4.00 Apr 10, 2008

Features

- High speed switching
- Capable of 5 V gate drive
- Low drive current
- High density mounting
- Low on-resistance

 $R_{DS(on)} = 2.6 \text{ m}\Omega \text{ typ.}$ (at $V_{GS} = 10 \text{ V}$)

Outline



Absolute Maximum Ratings

ltem	Symbol	Ratings	$\frac{(Ta = 25^{\circ}C)}{Unit}$
	-		
Drain to source voltage	V _{DSS}	30	V
Gate to source voltage	V _{GSS}	±20	V
Drain current	I _D	38	А
Drain peak current	Note1 D(pulse)	152	A
Body-drain diode reverse drain current	I _{DR}	38	А
Avalanche current	I _{AP} Note 2	19	А
Avalanche energy	E _{AR} Note 2	36.1	mJ
Channel dissipation	Pch Note3	45	W
Channel to ambient thermal impedance	θch-c ^{Note3}	2.78	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \ \mu s$, duty cycle $\le 1\%$

2. Value at Tch = 25° C, Rg $\geq 50 \Omega$

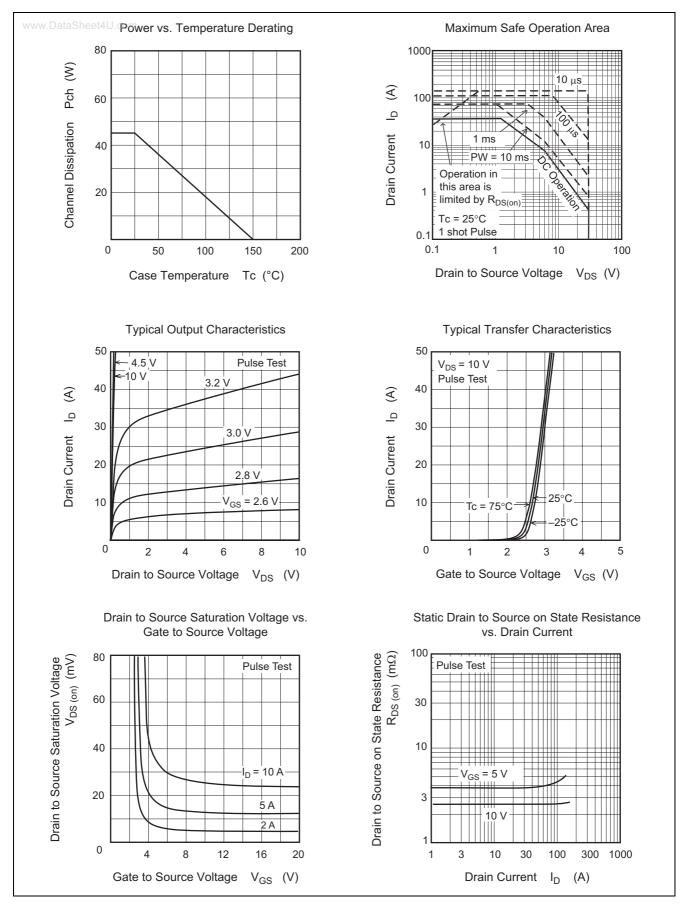
3. Tc = 25°C

Electrical Characteristics

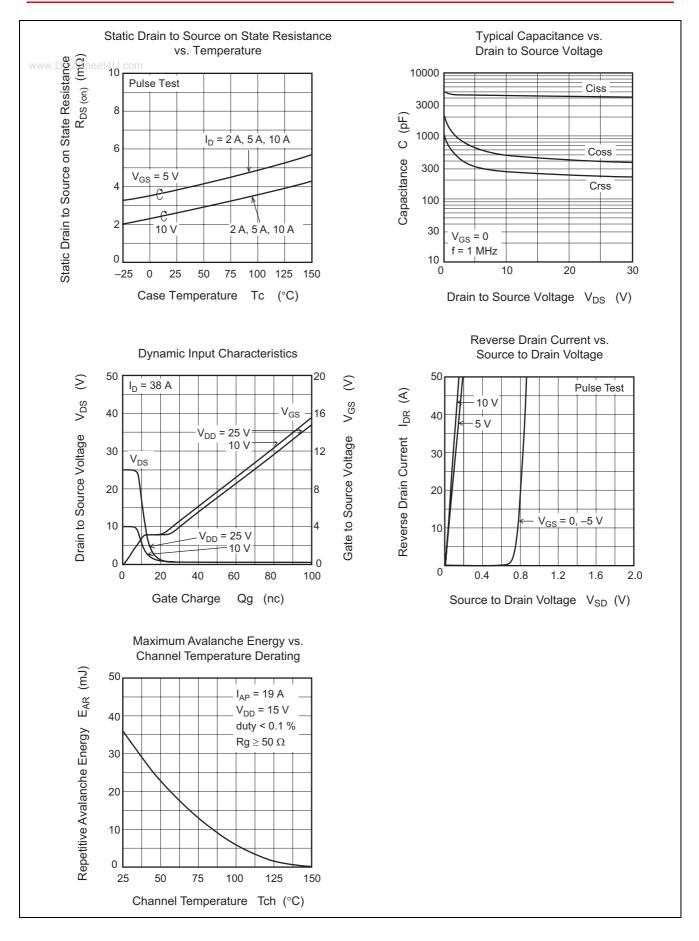
www.DataSheet4U.com	<u> </u>					$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	30		—	V	$I_D = 10 \text{ mA}, V_{GS} = 0$
Gate to source leak current	I _{GSS}		_	± 0.1	μΑ	$V_{GS} = \pm 20 V, V_{DS} = 0$
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 30 \text{ V}, V_{GS} = 0$
Gate to source cutoff voltage	V _{GS(off)}	1.0	_	2.5	V	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$
Static drain to source on state	R _{DS(on)}	_	2.6	3.4	mΩ	$I_D = 19 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$
resistance	R _{DS(on)}	_	3.8	5.4	mΩ	$I_D = 19 \text{ A}, V_{GS} = 5 \text{ V}^{Note4}$
Forward transfer admittance	y _{fs}		50	_	S	$I_D = 19 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$
Input capacitance	Ciss		4300	_	pF	V _{DS} = 10 V
Output capacitance	Coss		500	_	pF	V _{GS} = 0 f = 1 MHz
Reverse transfer capacitance	Crss		280	_	pF	
Total gate charge	Qg		33		nC	V _{DD} = 10 V V _{GS} = 5 V I _D = 38 A
Gate to source charge	Qgs		13	_	nC	
Gate to drain charge	Qgd	_	8	—	nC	
Turn-on delay time	t _{d(on)}	_	11	—	ns	$V_{GS} = 10 \text{ V}, I_D = 19 \text{ A}$
Rise time	tr	_	5.8	—	ns	$V_{DD} \cong 10 \text{ V}$ $R_{L} = 0.53 \Omega$ $Rg = 4.7 \Omega$
Turn-off delay time	t _{d(off)}	_	68	—	ns	
Fall time	t _f		12	_	ns	
Body-drain diode forward voltage	V_{DF}		0.84	1.10	V	$I_F = 38 \text{ A}, V_{GS} = 0^{\text{Note4}}$
Body-drain diode reverse recovery	t _{rr}	_	30	—	ns	I _F =38 A, V _{GS} = 0
time						di _F / dt = 100 A/ μs

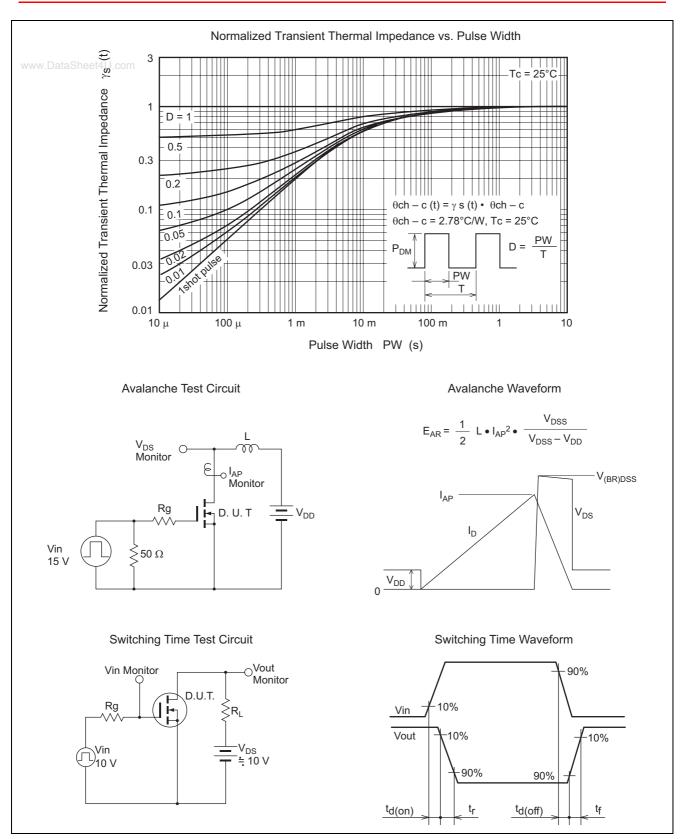
Notes: 4. Pulse test

Main Characteristics

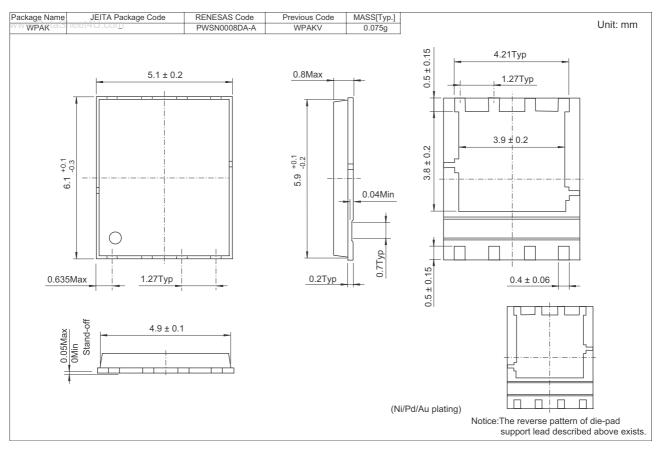


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Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
RJK0358DPA-00-J0	2500 pcs	Taping

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